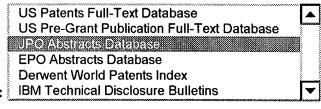


Search Results -

Term	Documents
AMORPHOUS.JPAB.	33546
AMORPHOU.JPAB.	2
SLICON JPAB.	29
SLICONS.JPAB.	1
CARBIDE.JPAB.	20487
CARBIDES.JPAB.	2197
A-SIC.JPAB.	284
A-SICS	0
INSULAT\$	0
INSULAT.JPAB.	183
((AMORPHOUS ADJ1 SLICON ADJ1 CARBIDE OR A-SIC) ADJ2 (INSULAT\$ OR DILECTRIC\$)).JPAB.	1

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Database:

(amorphous adjl slicon adjl carbide or a-SiC) adj2 (insulat\$ or dilectric\$)

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Search History

Today's Date: 9/22/2001

DB Name	Query	Hit Count	Set Name
JPAB	(amorphous adj1 slicon adj1 carbide or a-SiC) adj2 (insulat\$ or dilectric\$)	1	<u>L4</u>
USPT	(amorphous adj1 slicon adj1 carbide or a-SiC) adj2 (insulat\$ or dilectric\$)	0	<u>L3</u>
USPT	11 and (amorphous adj1 slicon adj1 carbide or a-SiC) adj2 (insulat\$ or dilectric\$)	0	<u>L2</u>
USPT	floating adj1 gate and transistor	7082	<u>L1</u>



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Search Results - Record(s) 1 through 1 of 1 returned.

1. Document ID: JP 60123074 A		
L4: Entry 1 of 1	File: JPAB	Jul 1, 1985
PUB-NO: JP360123074A		

PUBN-DATE: July 1, 1985

INVENTOR-INFORMATION:

NAME

COUNTRY

HAMA, TOSHIO

"US-CL-CURRENT: <u>136/244</u>; <u>136/258</u>

TITLE: AMORPHOUS SILICON SOLAR CELL

INT-CL (IPC): H01L 31/04

Full : Title : Citation Front	Review Classification Date Reference	Claims KWC Draw, Desc Image

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Term	Documents
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A-SICS	0
INSULAT\$	0
INSULAT.JPAB.	183
((AMORPHOUS ADJ1 SLICON ADJ1 CARBIDE OR A-SIC) ADJ2 (INSULAT\$ OR DILECTRIC\$)).JPAB.	1

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L4: Entry 1 of 1

File: JPAB

Jul 1, 1985

PUB-NO: JP360123074A

DOCUMENT-IDENTIFIER: JP 60123074 A TITLE: AMORPHOUS SILICON SOLAR CELL

PUBN-DATE: July 1, 1985

INVENTOR-INFORMATION:

NAME

COUNTRY

HAMA, TOSHIO

ASSIGNEE-INFORMATION:

NAME

COUNTRY

FUJI ELECTRIC CORP RES & DEV LTD

N/A

APPL-NO: JP58231798

APPL-DATE: December 8, 1983

US-CL-CURRENT: 136/244; 136/258

INT-CL (IPC): H01L 31/04

ABSTRACT:

PURPOSE: To shorten a manufacturing process for an insulating layer to a metallic substrate for an a-Si solar cell element formed on the substrate, and to reduce manufacturing cost by using an amorphous silicon carbide (a-SiC) layer as the insulating layer.

CONSTITUTION: A plurality of regions of insulating layers 2 consisting of a-SiC are shaped on a metallic substrate 1 while being mutually separated, N type a-Si layers 3 functioning as one electrodes are laminated on a plurality of the regions, I type a-Si layers 4 on regions, in which one parts of the N type layers are removed, and P type a-Si layers 5 on the layers 4 in succession, thus forming active layers 10 for mutually separated solar cell elements. The active layers 10, the outer circumferential surfaces of the insulating layers 2 and the exposed surfaces of the metallic substrate 1 are coated with an insulating film 6 consisting of a substance such as silicon oxide. The solar cell elements adjoining in succession are connected in series by forming transparent electrode layers 7 connecting sections 71 on the surfaces of the P type layers for each solar cell element and sections 72 on the exposed surfaces of the N type layers for adjacent elements. The active layers 10 may be laminated in orer of P types, I types and N types from the insulating layers 2 sides.

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